

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS E6

600V CoolMOS™ E6 Power Transistor  
IPx60R190E6

## Data Sheet

Rev. 2.0, 2010-05-03  
Final

Industrial & Multimarket

## 600V CoolMOS™ E6 Power Transistor

IPP60R190E6, IPA60R190E6  
IPW60R190E6

### 1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ E6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.

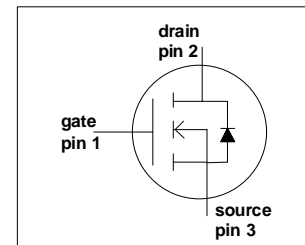
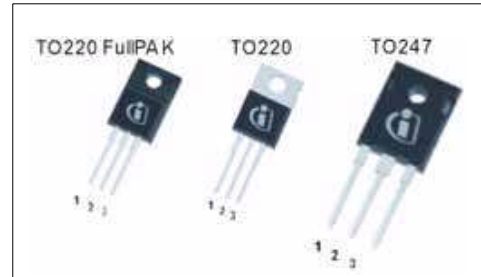
#### Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC<sup>1)</sup> qualified, Pb-free plating, Halogen free

#### Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.19	$\Omega$
$Q_{g,typ}$	63	nC
$I_{D,pulse}$	59	A
$E_{oss} @ 400V$	5.2	$\mu J$
Body diode $di/dt$	500	A/ $\mu s$

Type / Ordering Code	Package	Marking	Related Links
IPW60R190E6	PG-TO247	6R190E6	<a href="#">IFX CoolMOS Webpage</a> <a href="#">IFX Design tools</a>
IPP60R190E6	PG-TO220		
IPA60R190E6	PG-TO220 FullPAK		

1) J-STD20 and JESD22

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## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	20.2	A	$T_C = 25\text{ °C}$
				12.8		$T_C = 100\text{ °C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	59	A	$T_C = 25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	418	mJ	$I_D = 3.4\text{ A}$ , $V_{DD} = 50\text{ V}$ (see table 20)
Avalanche energy, repetitive	$E_{AR}$	-	-	0.63		$I_D = 3.4\text{ A}$ , $V_{DD} = 50\text{ V}$
Avalanche current, repetitive	$I_{AR}$	-	-	3.4	A	
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 480\text{ V}$
Gate source voltage	$V_{GS}$	-20	-	20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Power dissipation for TO-220, TO-247	$P_{tot}$	-	-	151	W	$T_C = 25\text{ °C}$
Power dissipation for TO-220 FullPAK	$P_{tot}$	-	-	34		
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	
Mounting torque TO-220, TO-247		-	-	60	Ncm	M3 and M3.5 screws
Mounting torque TO-220 FullPAK				50		M2.5 screws
Continuous diode forward current	$I_S$	-	-	17.5	A	$T_C = 25\text{ °C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	59	A	$T_C = 25\text{ °C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 400\text{ V}$ , $I_{SD} \leq I_D$ , $T_j = 25\text{ °C}$
Maximum diode commutation speed <sup>3)</sup>	di <sub>r</sub> /dt			500	A/μs	(see table 21)

1) Limited by  $T_{j,max}$ . Maximum duty cycle  $D = 0.75$

2) Pulse width  $t_p$  limited by  $T_{j,max}$

3) Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics TO-220 (IPP60R190E6), TO-247 (IPW60R190E6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.83	°C/W	
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

**Table 4 Thermal characteristics TO-220 FullPAK (IPA60R190E6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	3.7	°C/W	
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	80		leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

## 4 Electrical characteristics

Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified.

**Table 5 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=0.25\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5		$V_{DS}=V_{GS}$ , $I_D=0.63\text{ mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$
		-	10	-		$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=150\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.17	0.190	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=9.5\text{ A}$ , $T_j=25\text{ °C}$
		-	0.44	-		$V_{GS}=10\text{ V}$ , $I_D=9.5\text{ A}$ , $T_j=150\text{ °C}$
Gate resistance	$R_G$	-	6	-	$\Omega$	$f=1\text{ MHz}$ , open drain

**Table 6 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	1400	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	85	-		
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	56	-		
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	266	-		$I_D=\text{constant}$ , $V_{GS}=0\text{ V}$ $V_{DS}=0\dots480\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=400\text{ V}$ , $V_{GS}=13\text{ V}$ , $I_D=9.5\text{ A}$ , $R_G=3.4\text{ }\Omega$ (see table 19)
Rise time	$t_r$	-	10	-		
Turn-off delay time	$t_{d(off)}$	-	90	-		
Fall time	$t_f$	-	8	-		

1)  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

2)  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

**Table 7 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	7.6	-	nC	$V_{DD}=480\text{ V}$ , $I_D=9.5\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	32	-		
Gate charge total	$Q_g$	-	63	-		
Gate plateau voltage	$V_{\text{plateau}}$	-	5.4	-	V	

**Table 8 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0\text{ V}$ , $I_F=9.5\text{ A}$ , $T_j=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	430	-	ns	$V_R=400\text{ V}$ , $I_F=9.5\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$ (see table 22)
Reverse recovery charge	$Q_{rr}$	-	6.9	-	$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$	-	30	-	A	

5 Electrical characteristics diagrams

Table 9

Power dissipation TO-220, TO-247	Power dissipation TO-220 FullPAK
$P_{tot} = f(T_c)$	$P_{tot} = f(T_c)$

Table 10

Max. transient thermal impedance TO-220, TO-247	Max. transient thermal impedance TO-220 FullPAK
$Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p/T$	$Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p/T$



Table 11

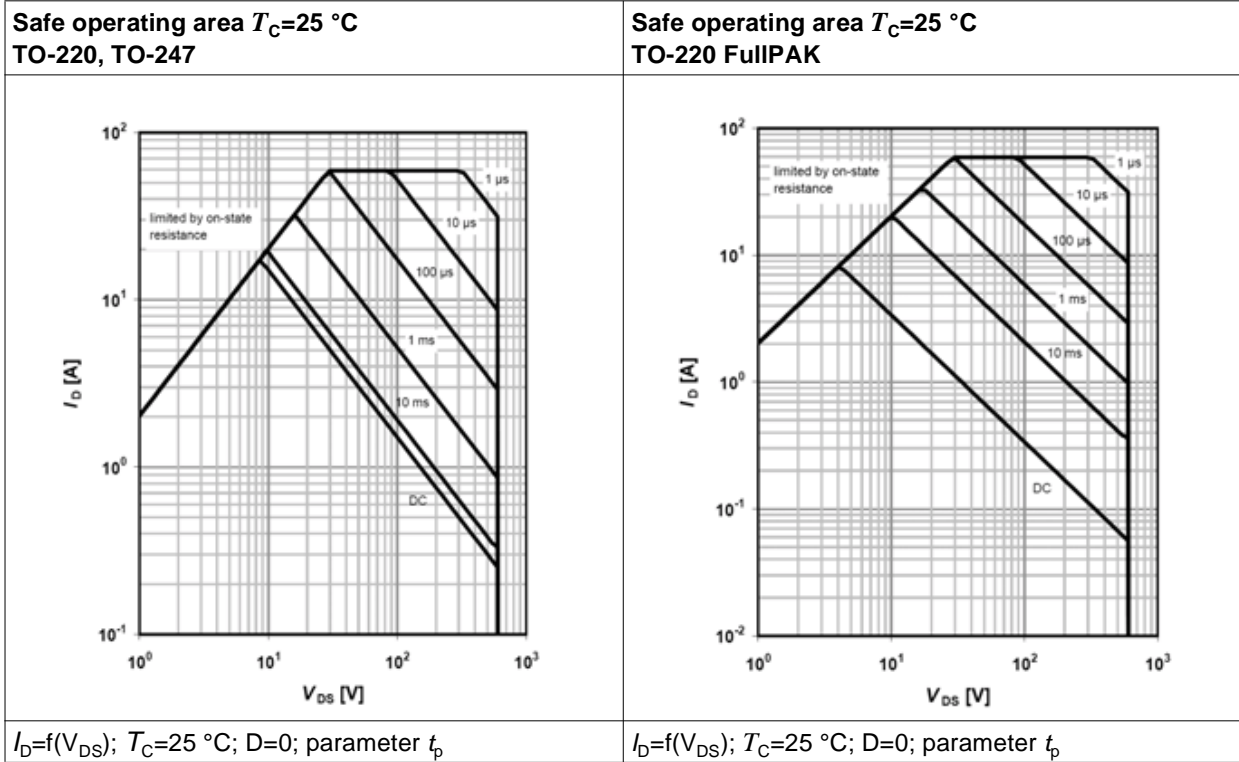


Table 12

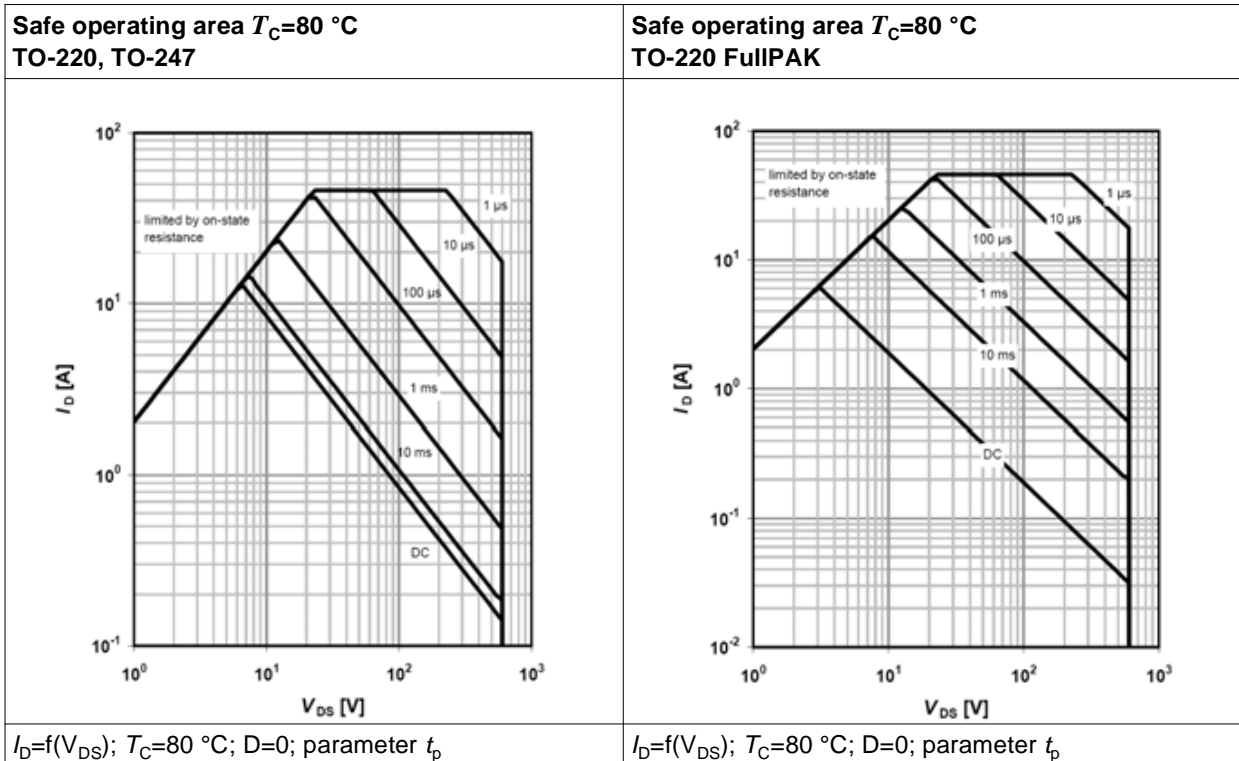


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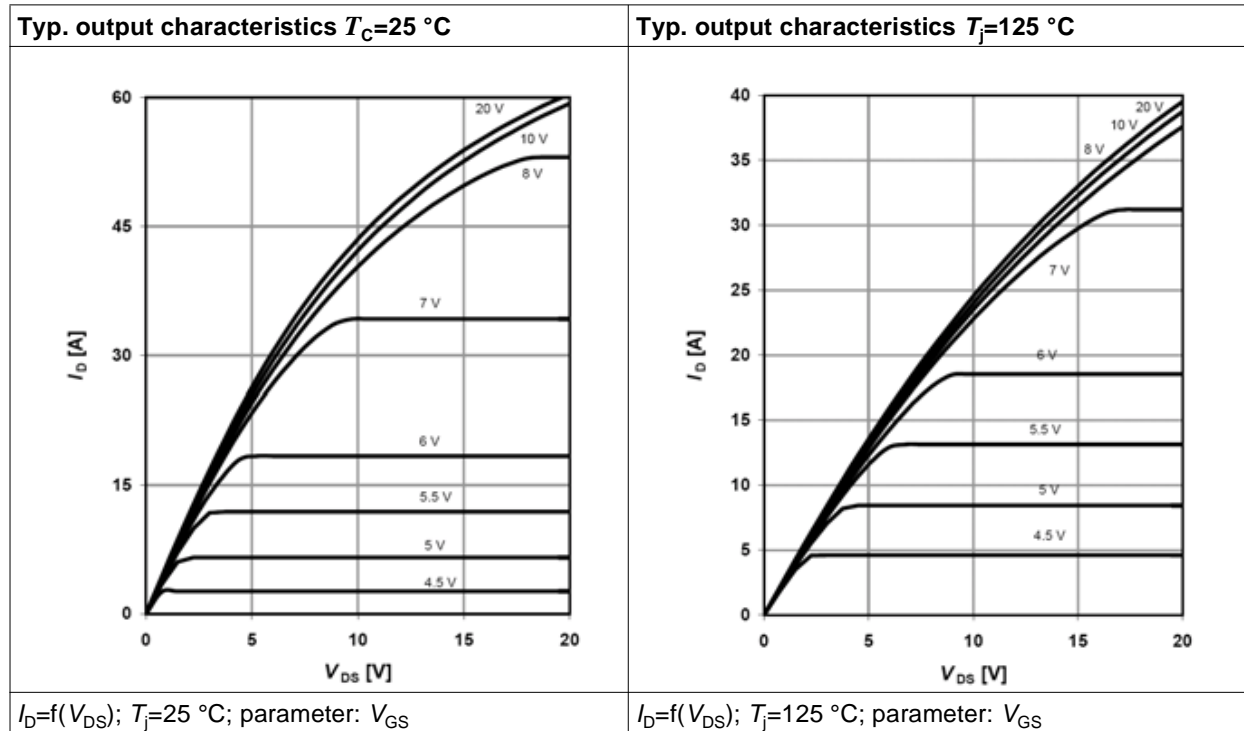


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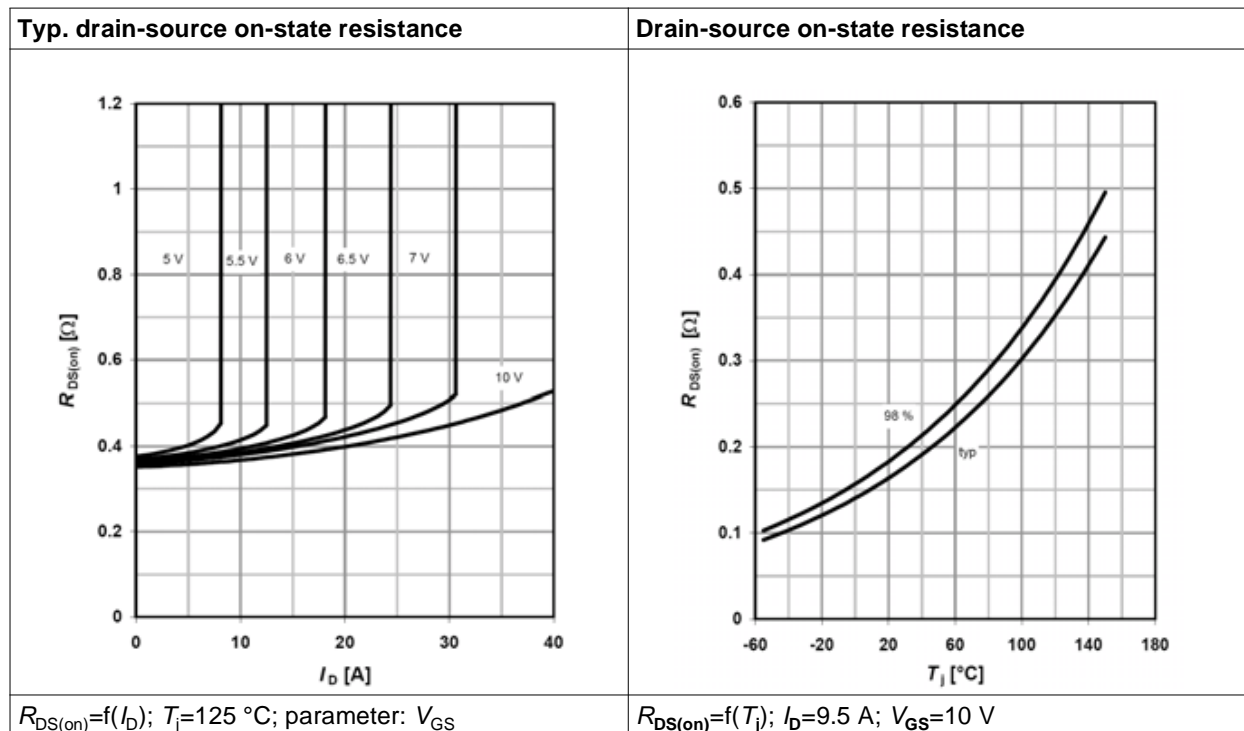


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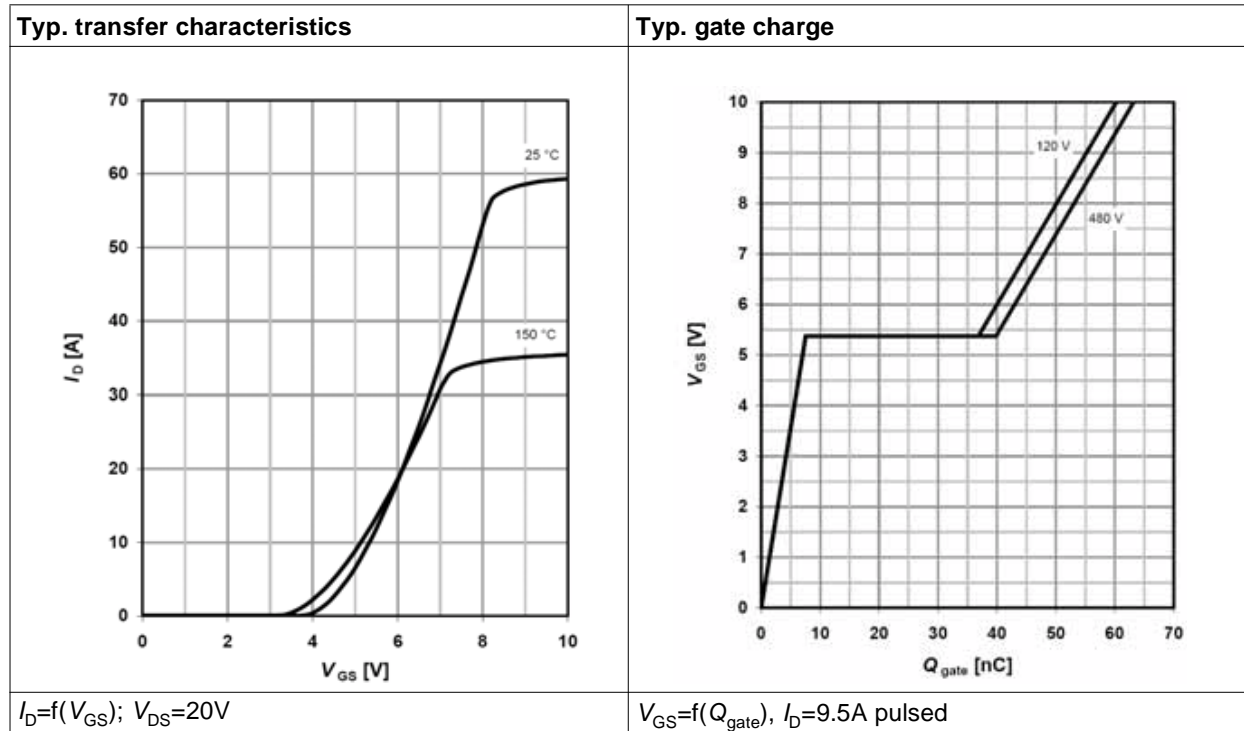


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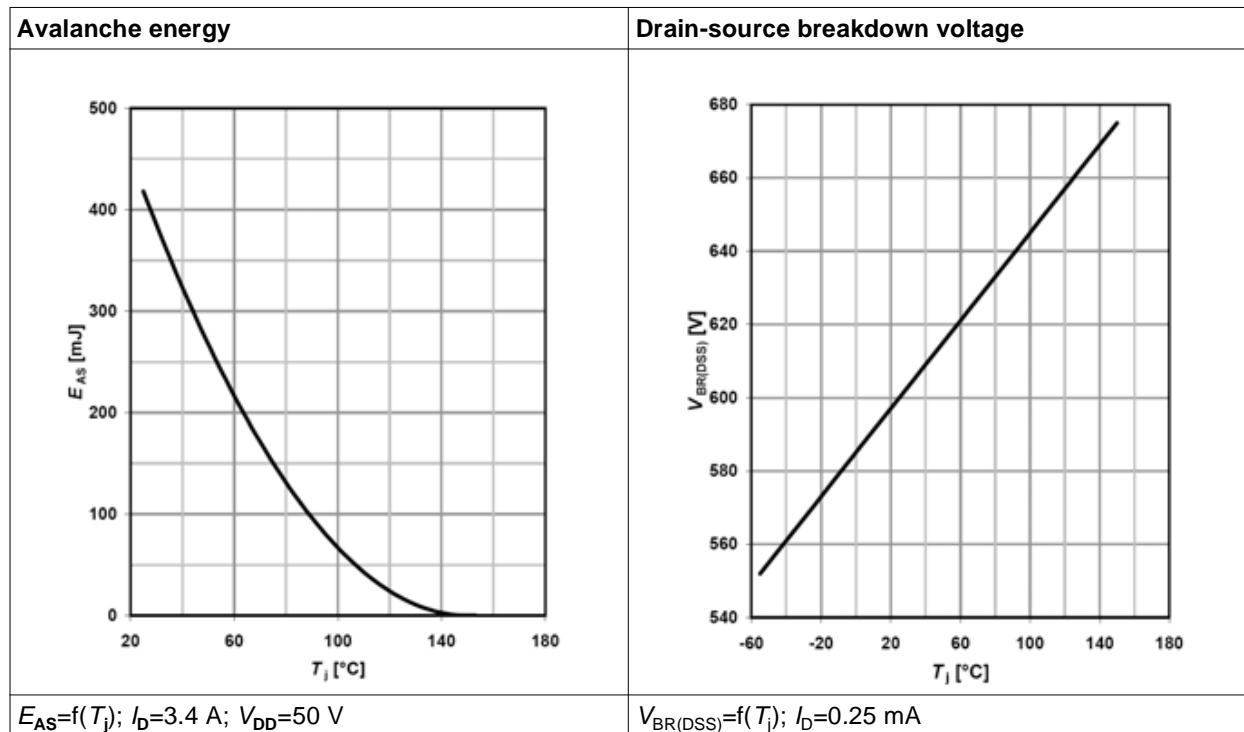


Table 17

Typ. capacitances	Typ. $C_{oss}$ stored energy
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$	$E_{Oss}=f(V_{DS})$

Table 18

Forward characteristics of reverse diode
$I_F=f(V_{SD}); \text{parameter: } T_j$

## 6 Test circuits

Table 19 Switching times test circuit and waveform for inductive load

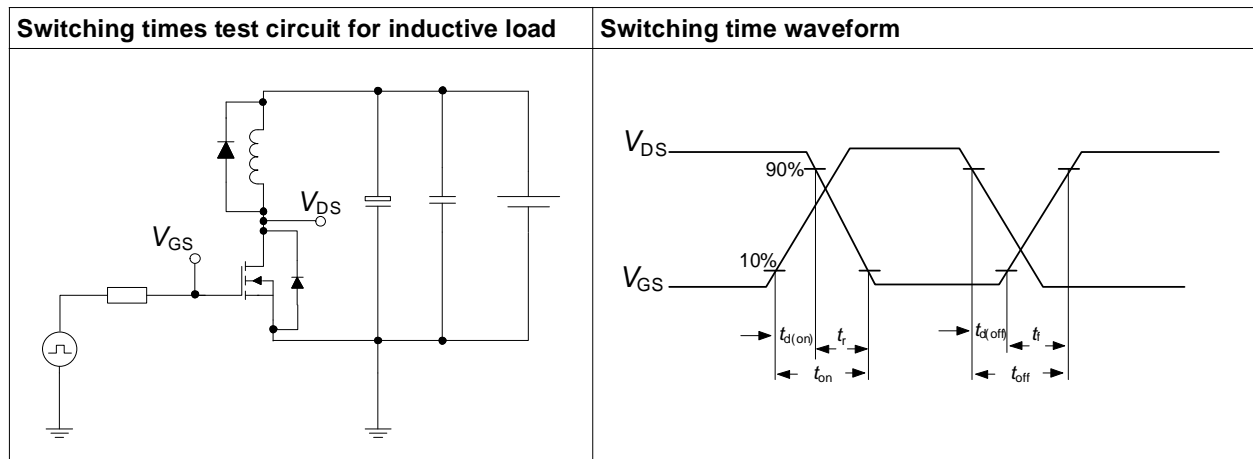


Table 20 Unclamped inductive load test circuit and waveform

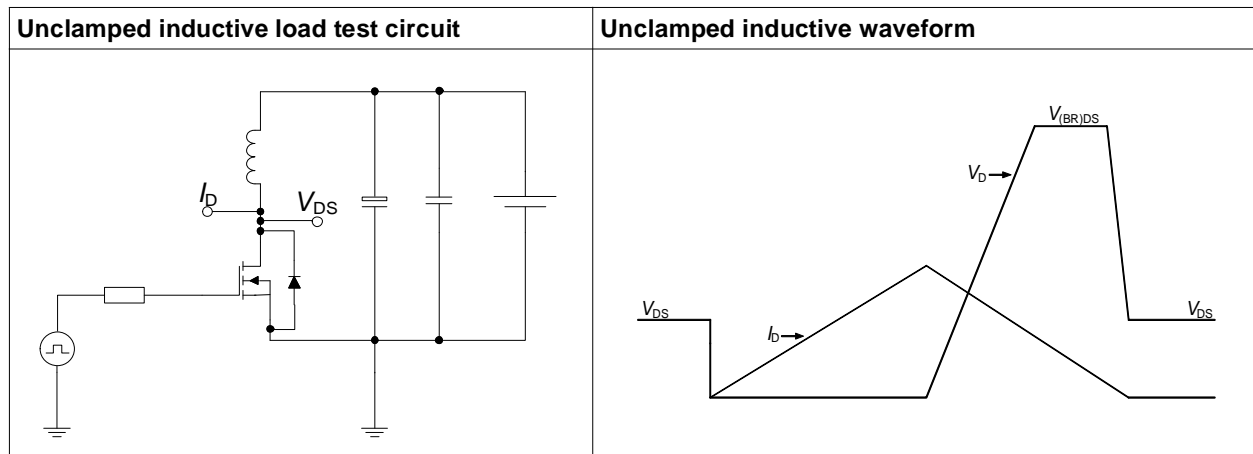
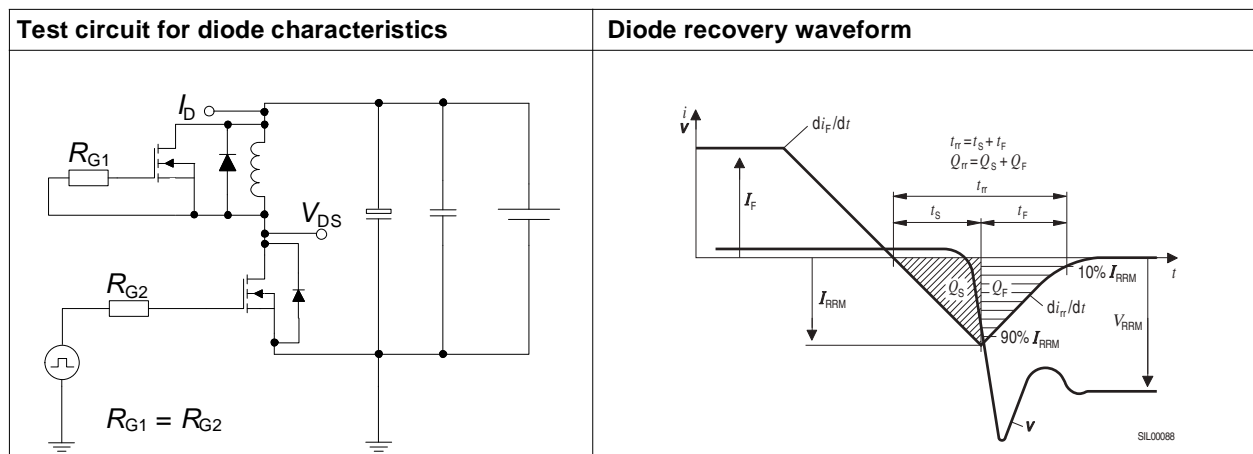


Table 21 Test circuit and waveform for diode characteristics



7 Package outlines

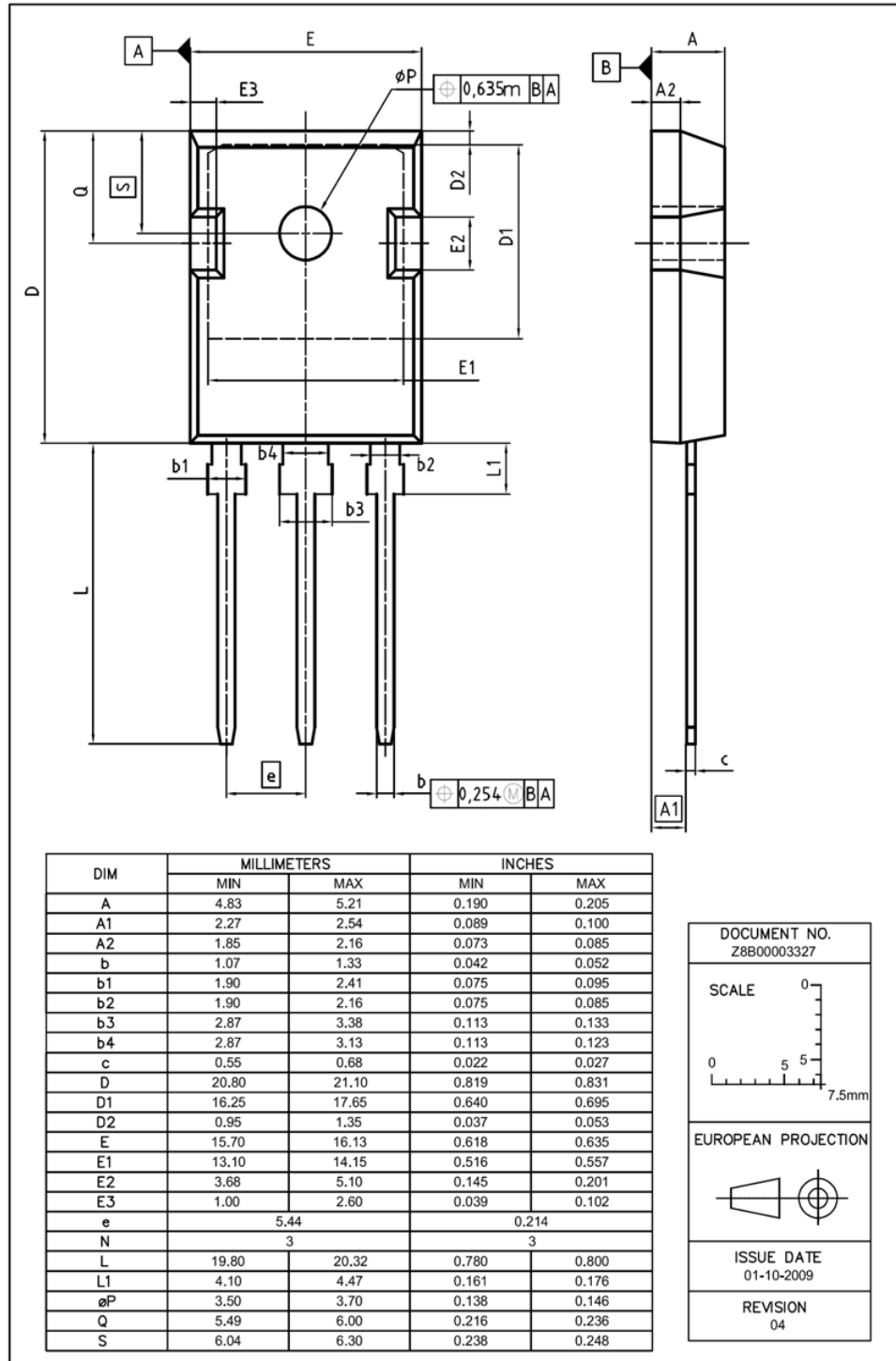
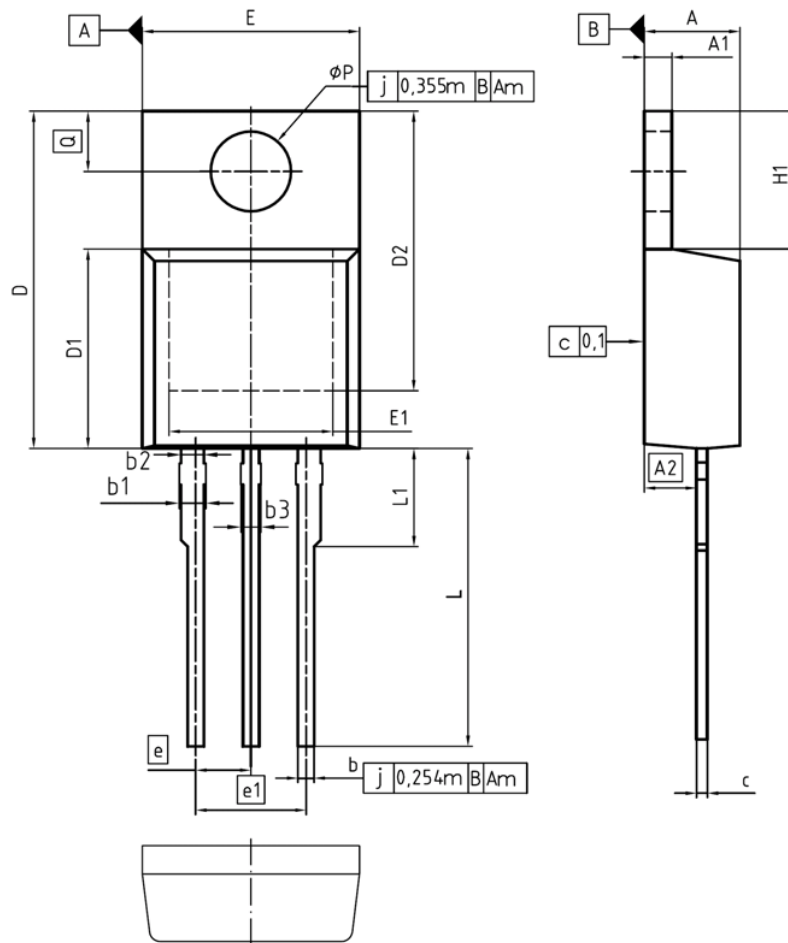


Figure 1 Outlines TO-247, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
φP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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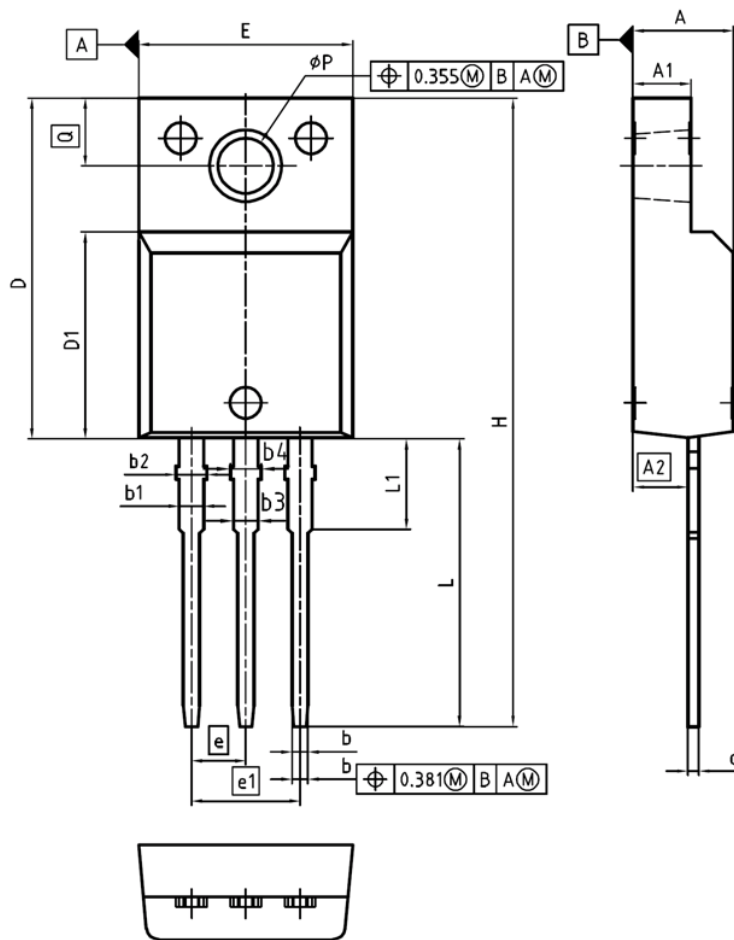
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Figure 2 Outlines TO-220, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
φP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

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Figure 3 Outlines TO-220 FullIPAK, dimensions in mm/inches



## 8 Revision History

### CoolMOS E6 600V CoolMOS™ E6 Power Transistor

#### Revision History: 2010-05-03, Rev. 2.0

Revision	Subjects (major changes since last revision)
2.0	Release of final data sheet

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